

## Silicon NPN Power Transistors

## 2SC2565

## DESCRIPTION

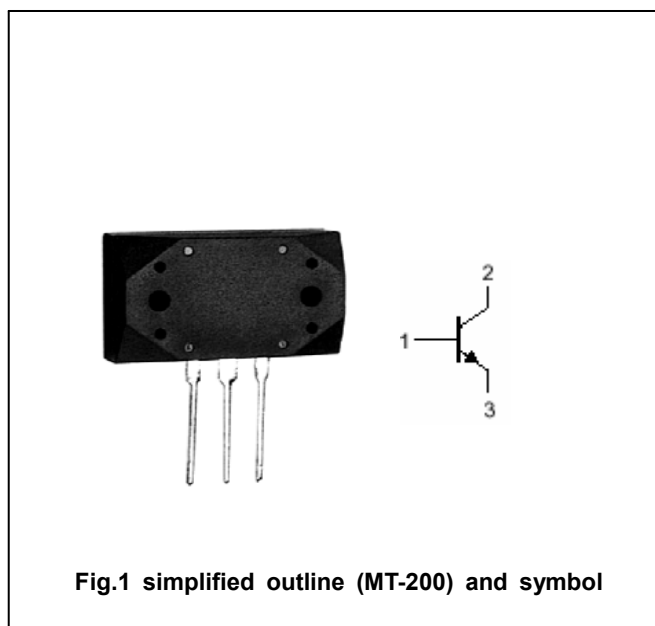
- With MT-200 package
- Complement to type 2SA1095
- High transition frequency

## APPLICATIONS

- For power amplifier applications

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



## Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	160	V
$V_{CEO}$	Collector-emitter voltage	Open base	160	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		15	A
$I_B$	Base current		1.5	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	150	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

## Silicon NPN Power Transistors

## 2SC2565

## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=0.1A$ ; $I_B=0$	160			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10mA$ ; $I_C=0$	5			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=5A$ ; $I_B=0.5A$			2.0	V
$V_{BE}$	Base-emitter on voltage	$I_C=5A$ ; $V_{CE}=5V$			2.0	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=160V$ ; $I_E=0$			50	$\mu A$
$I_{EBO}$	Emitter cut-off current	$V_{EB}=5V$ ; $I_C=0$			50	$\mu A$
$h_{FE-1}$	DC current gain	$I_C=1A$ ; $V_{CE}=5V$	55		240	
$h_{FE-2}$	DC current gain	$I_C=5A$ ; $V_{CE}=5V$	40			
$f_T$	Transition frequency	$I_C=1A$ ; $V_{CE}=10V$		80		MHz
$C_{OB}$	Output capacitance	$I_E=0$ ; $V_{CB}=10V$ ; $f=1MHz$		200		pF

◆  $h_{FE-1}$  classifications

R	O	Y
55-110	80-160	120-240

## Silicon NPN Power Transistors

2SC2565

## PACKAGE OUTLINE

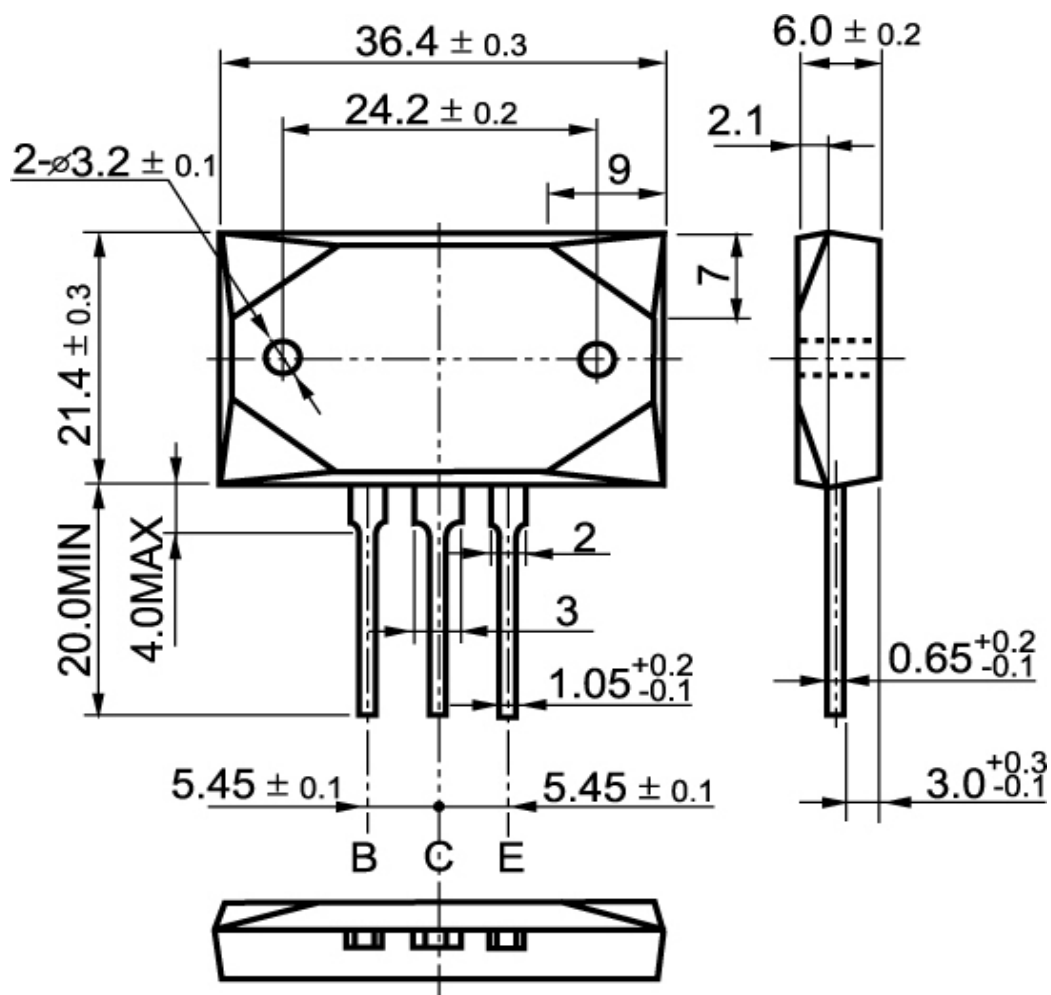


Fig.2 Outline dimensions